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Supplement of

Siloxane treatment of metal oxide semiconductor gas sensors in temperature-cycled operation – sensitivity and selectivity

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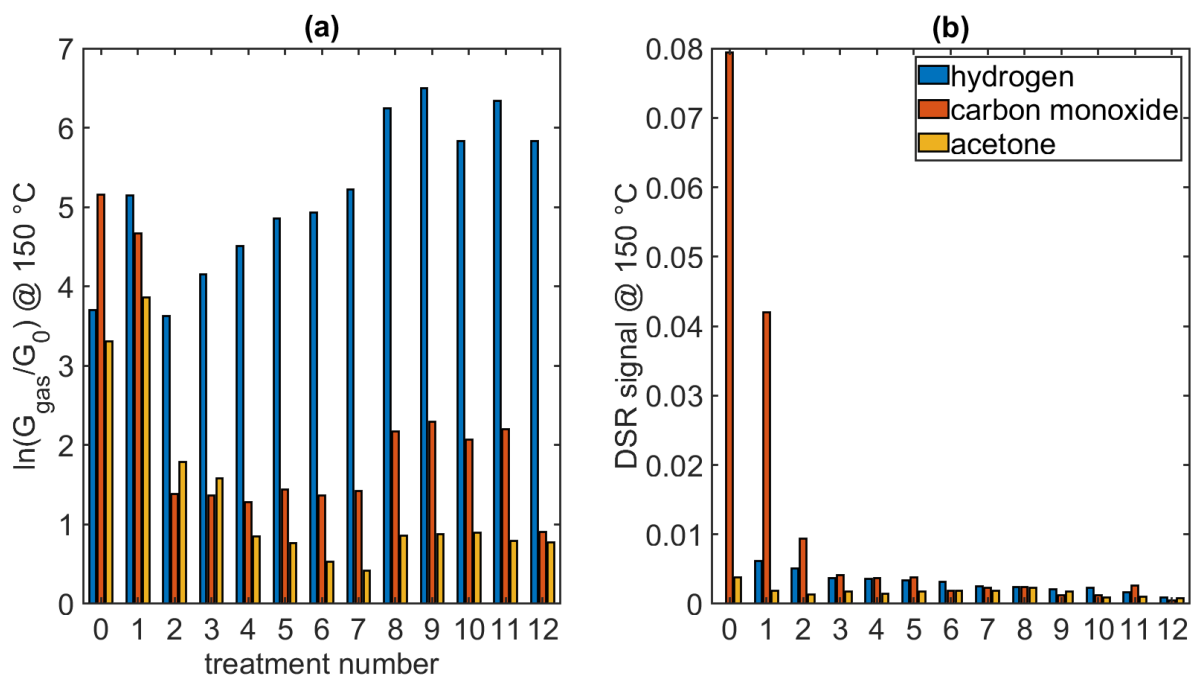


Figure S1: (a) The quasistatic sensor response at the end of the 150 °C phase for the three measured gases at 2 ppm over the treatment process. (b) The DSR signal on the 150 °C phase for the three measured gases at 2 ppm over the treatment process.

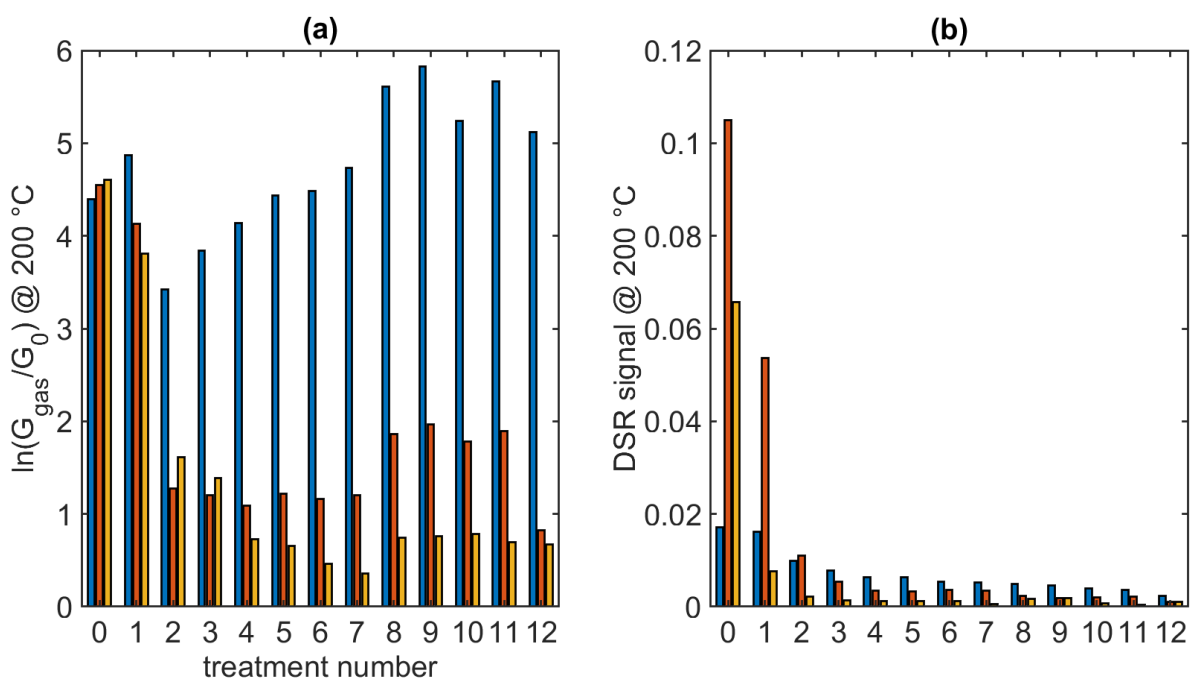


Figure S2: (a) The quasistatic sensor response at the end of the 200 °C phase for the three measured gases at 2 ppm over the treatment process. (b) The DSR signal on the 200 °C phase for the three measured gases at 2 ppm over the treatment process.

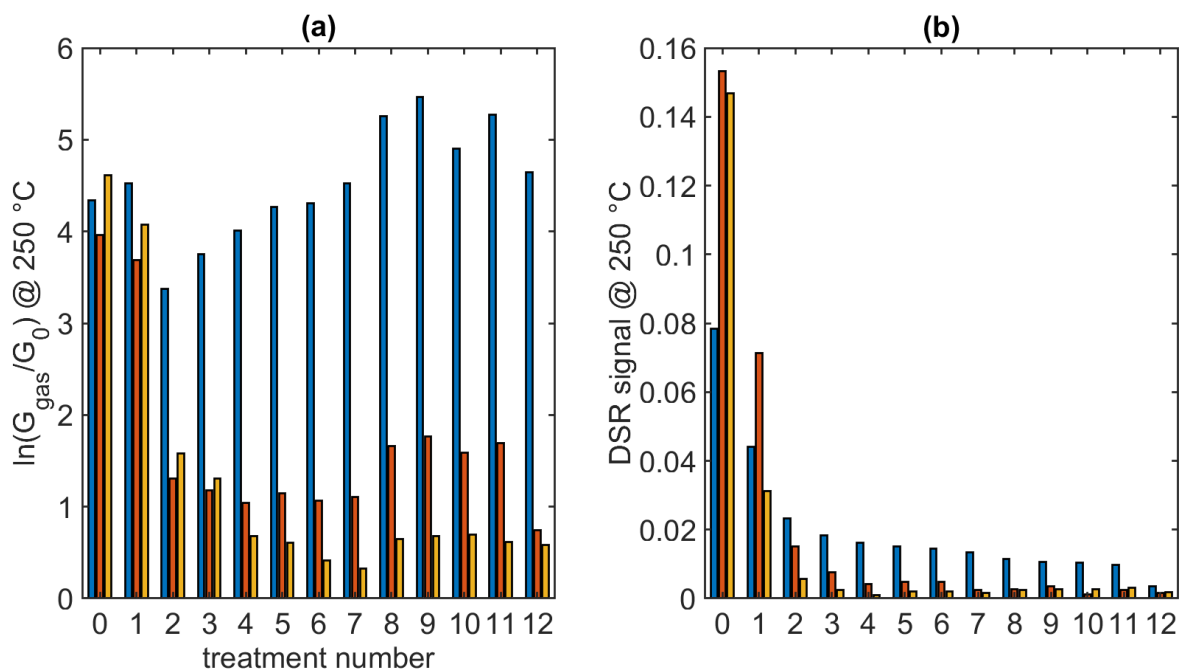


Figure S3: (a) The quasistatic sensor response at the end of the 250 °C phase for the three measured gases at 2 ppm over the treatment process. (b) The DSR signal on the 250 °C phase for the three measured gases at 2 ppm over the treatment process.

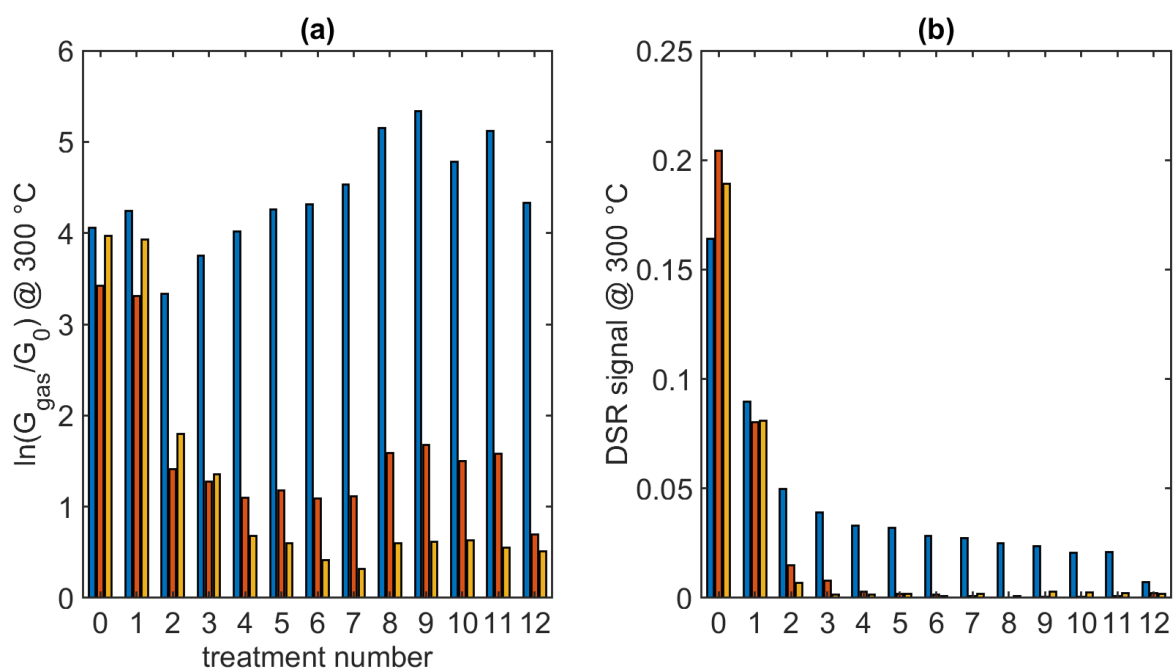


Figure S4: (a) The quasistatic sensor response at the end of the 300 °C phase for the three measured gases at 2 ppm over the treatment process. (b) The DSR signal on the 300 °C phase for the three measured gases at 2 ppm over the treatment process.

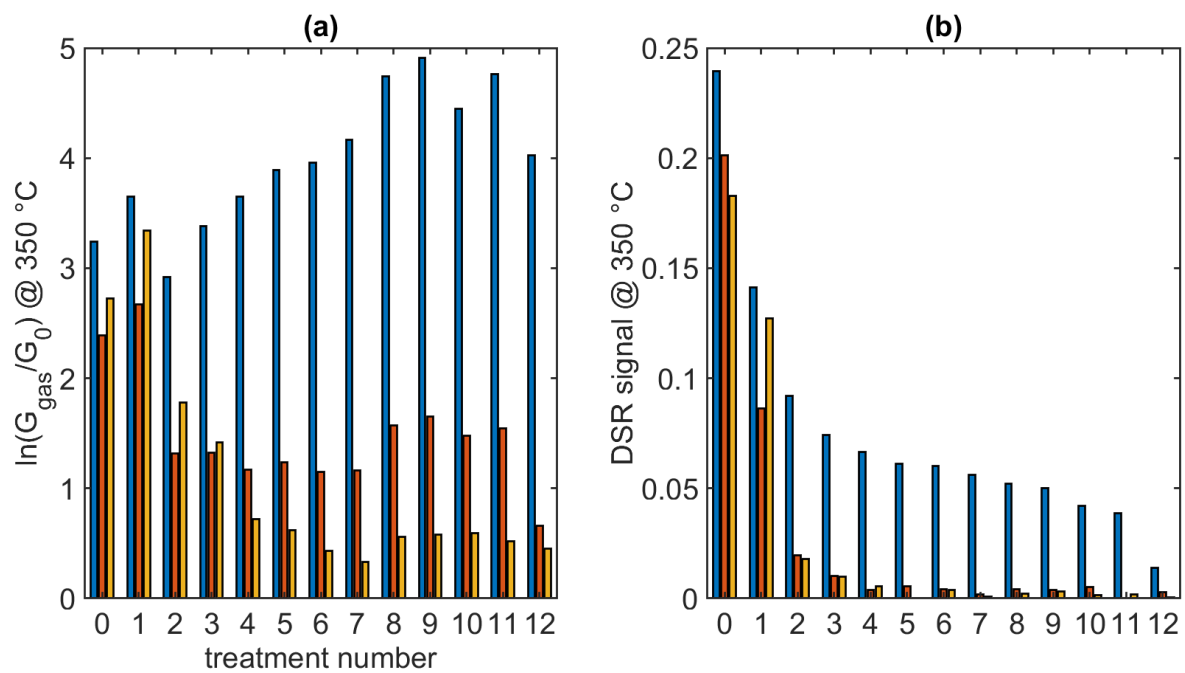


Figure S5: (a) The quasistatic sensor response at the end of the 350 °C phase for the three measured gases at 2 ppm over the treatment process. (b) The DSR signal on the 350 °C phase for the three measured gases at 2 ppm over the treatment process.